N-Channel Enhancement Mode Power MOSFET

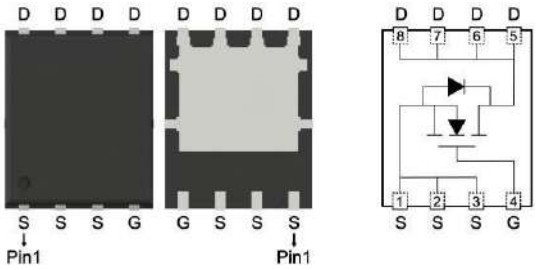
Product Summary

BV_{DSS}	150	V
$R_{DS(ON)}$ typ. @ V_{GS}=10V, I_D=10A	10	mΩ
$R_{DS(ON)}$ typ. @ V_{GS}=4.5V, I_D=8A	13	
I_D @ V_{GS}=10V, T_C=25°C	57	A
I_D @ V_{GS}=10V, T_A=25°C	10	

Features

- Low On Resistance
- Low Gate Charge
- Fast Switching Characteristic
- Pb-free lead plating and halogen-free

DFN5×6



Marking

← Device Code

← Date Code

YMXX: Date Code Marking
Y: Year Code, the last digit of Christian year
M: Month Code

A: Jan	B: Feb	C: Mar	D: Apr	E: May	F: Jun
G: Jul	H: Aug	J: Sep	K: Oct	L: Nov	M: Dec

XX: Production Serial Number, 01~99

Ordering Information

Device	Package	Shipping
KPRB011N15R	DFN5×6	3000pcs / Tape & Reel

0: Product rank, zero for no rank products.
T6: Packing spec, T6 : 3000pcs / tape & reel, 13" reel
G: Environment friendly grade: S for RoHS compliant products, G for RoHS compliant and green compound products.

Absolute Maximum Ratings (T_A=25°C)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	150	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current @ V_{GS}=10V, T_C=25°C	*a	I_D	57	A
Continuous Drain Current @ V_{GS}=10V, T_C=100°C	*a		36	
Continuous Drain Current @ V_{GS}=10V, T_A=25°C	*b		10	
Continuous Drain Current @ V_{GS}=10V, T_A=70°C	*b		8	
Pulsed Drain Current	*c	I_{DM}	228	
Continuous Body Diode Forward Current @ T_C=25°C	*a	I_S	57	
Pulsed Body Diode Forward Current @ T_C=25°C	*a	I_{SM}	228	
Avalanche Current @ L=0.1mH		I_{AS}	32	
Avalanche Energy @ L=0.5mH		E_{AS}	110	mJ
Total Power Dissipation	T_C=25°C *a	P_D	96	W
	T_C=100°C *a		34	
	T_A=25°C *b		2.8	
	T_A=70°C *b		1.8	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55~+150	°C
Steady State Thermal Resistance, Junction-to-Case		$R_{\theta JC}$	1.3	°C/W
Steady State Thermal Resistance, Junction-to-Ambient	*b	$R_{\theta JA}$	45	

Electrical Characteristics (T_A=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	150	-	-	V	V_{GS}=0V, I_D=250μA
$V_{GS(th)}$	1	-	2.5		V_{DS}=V_{GS}, I_D=250μA
G_{FS}	-	29	-	S	V_{DS}=10V, I_D=10A
I_{GSS}	-	-	±100	nA	V_{GS}=±20V, V_{DS}=0V
I_{DSS}	-	-	1	μA	V_{DS}=120V, V_{GS}=0V
$R_{DS(ON)}$	-	10	13	mΩ	V_{GS}=10V, I_D=10A
	-	13	18		V_{GS}=4.5V, I_D=8A
Dynamic					
C_{iss}	-	4335	-	pF	V_{DS}=75V, V_{GS}=0V, f=1MHz
C_{oss}	-	270	-		
C_{rss}	-	70	-		
R_g	-	1	-	Ω	f=1MHz
Q_g *d,e	-	43	-	nC	V_{DS}=75V, I_D=10A, V_{GS}=4.5V
Q_g *d,e	-	82	-		V_{DS}=75V, I_D=10A, V_{GS}=10V
Q_{gs} *d,e	-	14	-		
Q_{gd} *d,e	-	19	-		
$t_{d(ON)}$ *d,e	-	26	-	ns	V_{DS}=75V, I_D=10A, V_{GS}=10V, R_{GS}=1Ω
tr *d,e	-	23	-		
$t_{d(OFF)}$ *d,e	-	81	-		
t_f *d,e	-	13	-		
Source-Drain Diode					
V_{SD} *d	-	0.79	1.2	V	I_S=10A, V_{GS}=0V
t_{rr}	-	72	-	ns	I_F=10A, di/dt=100A/μs
Q_{rr}	-	220	-	nC	

Note:

*a. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper Dissipation.

*b. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz copper, in a still air environment with T_A=25°C. The power dissipation P_D is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

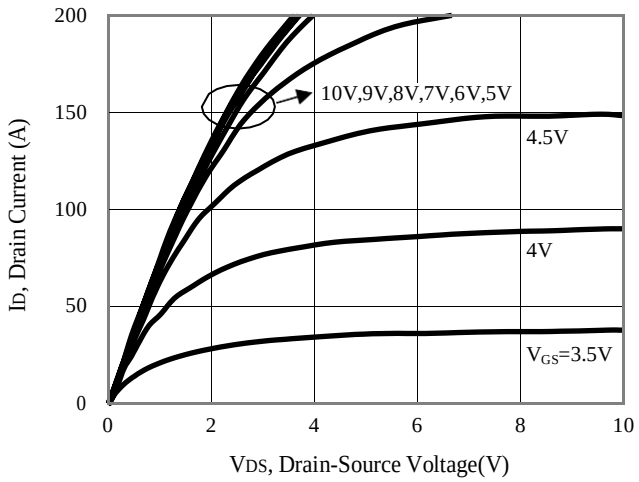
*c. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C. Ratings are based on low frequency and low duty cycles to keep initial T_J=25°C.

*d. Pulse Test : Pulse Width≤300μs, Duty Cycle≤2%.

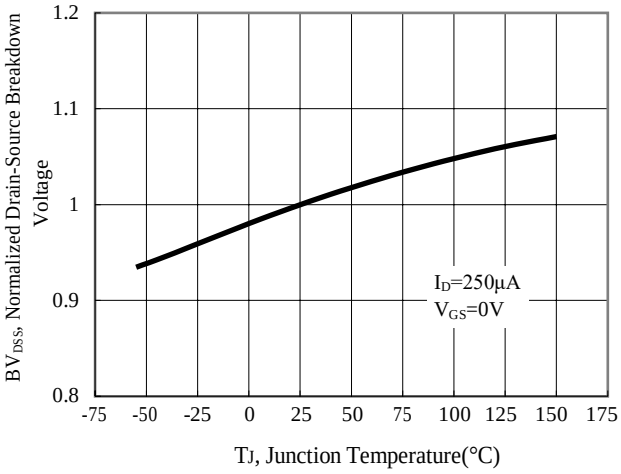
*e. Independent of operating temperature.

Typical Characteristics

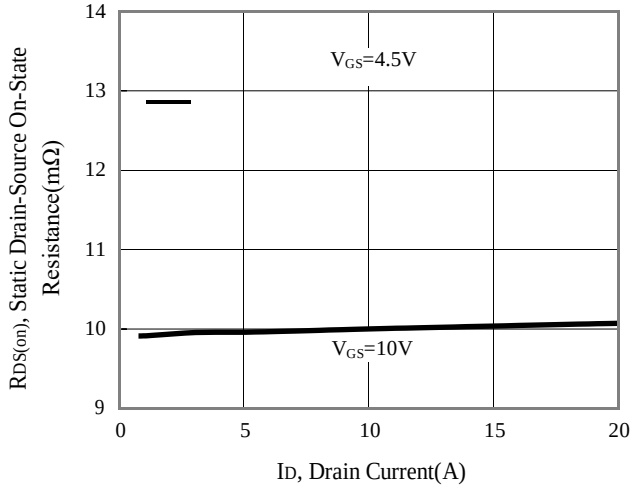
Typical Output Characteristics



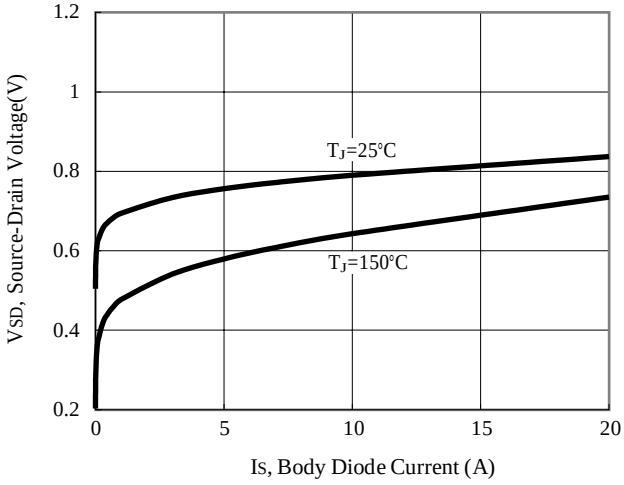
Breakdown Voltage vs Ambient Temperature



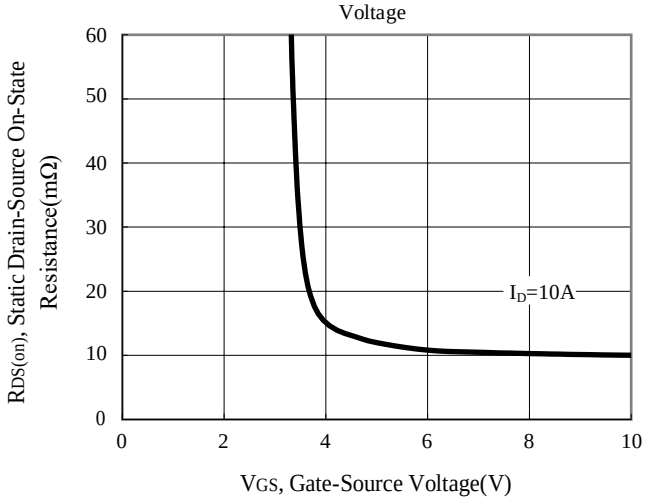
Static Drain-Source On-State resistance vs Drain Current



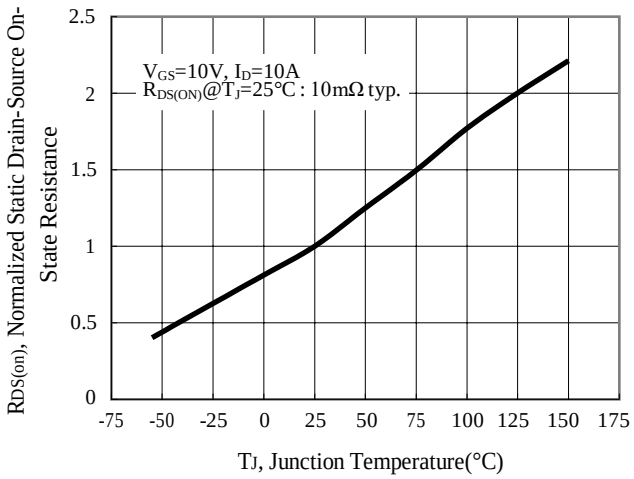
Body Diode Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

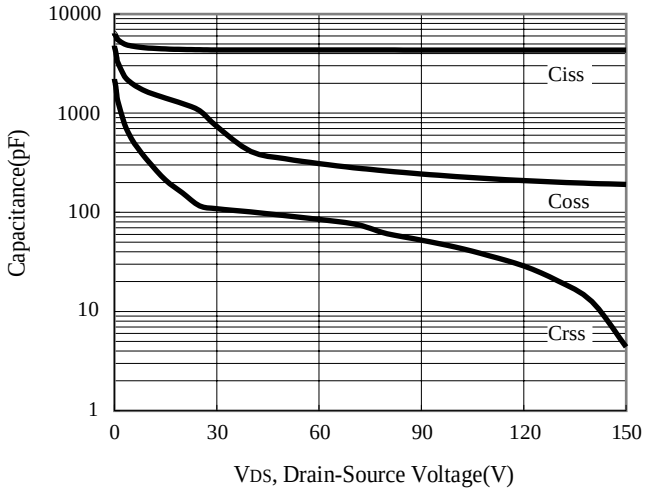


Drain-Source On-State Resistance vs Junction Temperature

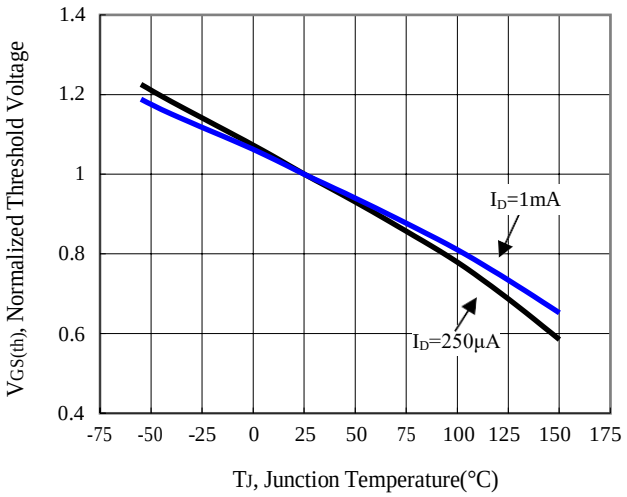


Typical Characteristics

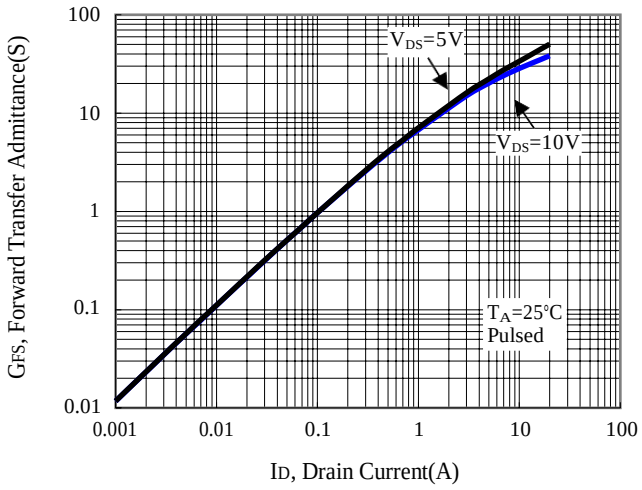
Capacitance vs Drain-to-Source Voltage



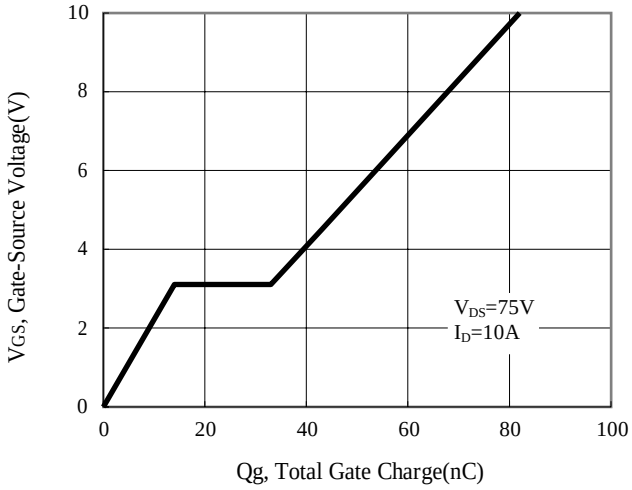
Threshold Voltage vs Junction Temperature



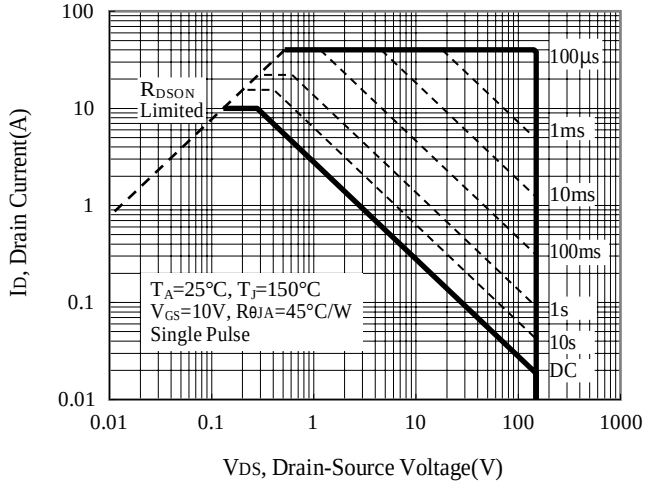
Forward Transfer Admittance vs Drain Current



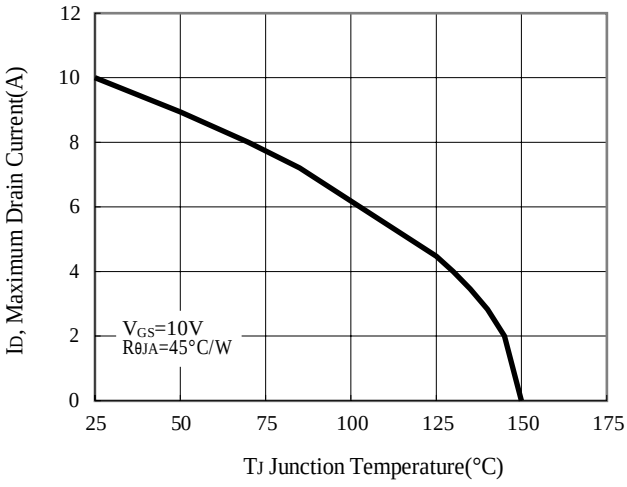
Gate Charge Characteristics



Maximum Safe Operating Area

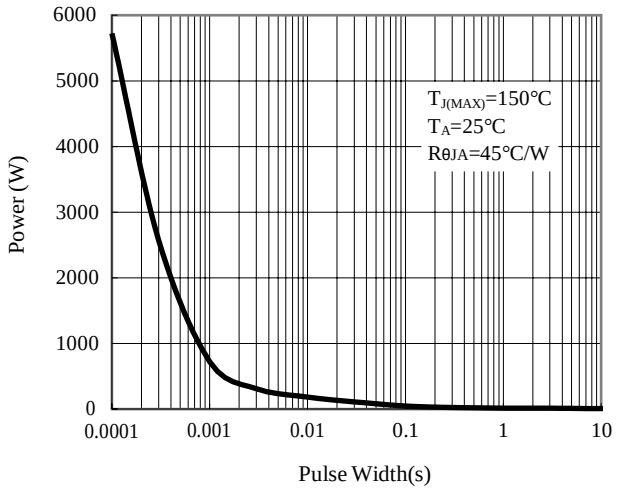


Maximum Drain Current vs Junction Temperature

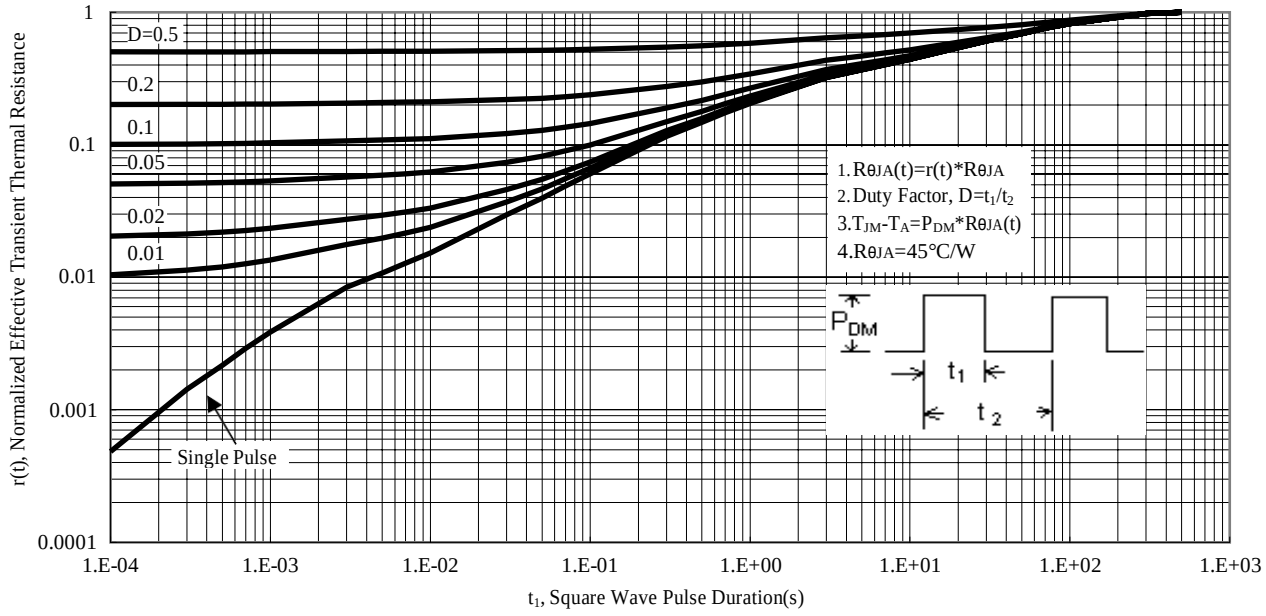


Typical Characteristics

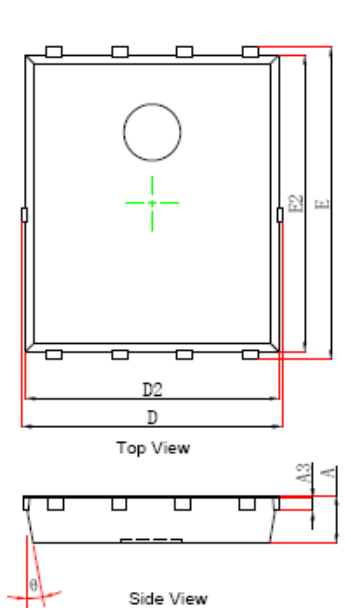
Single Pulse Power Rating, Junction to Ambient

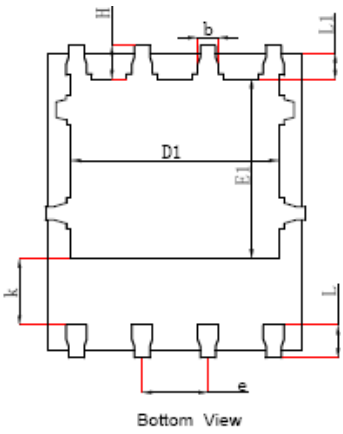


Transient Thermal Response Curves

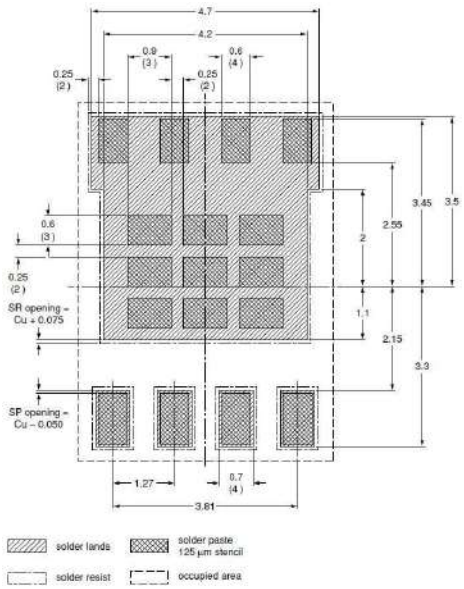


DFN5×6 Dimension





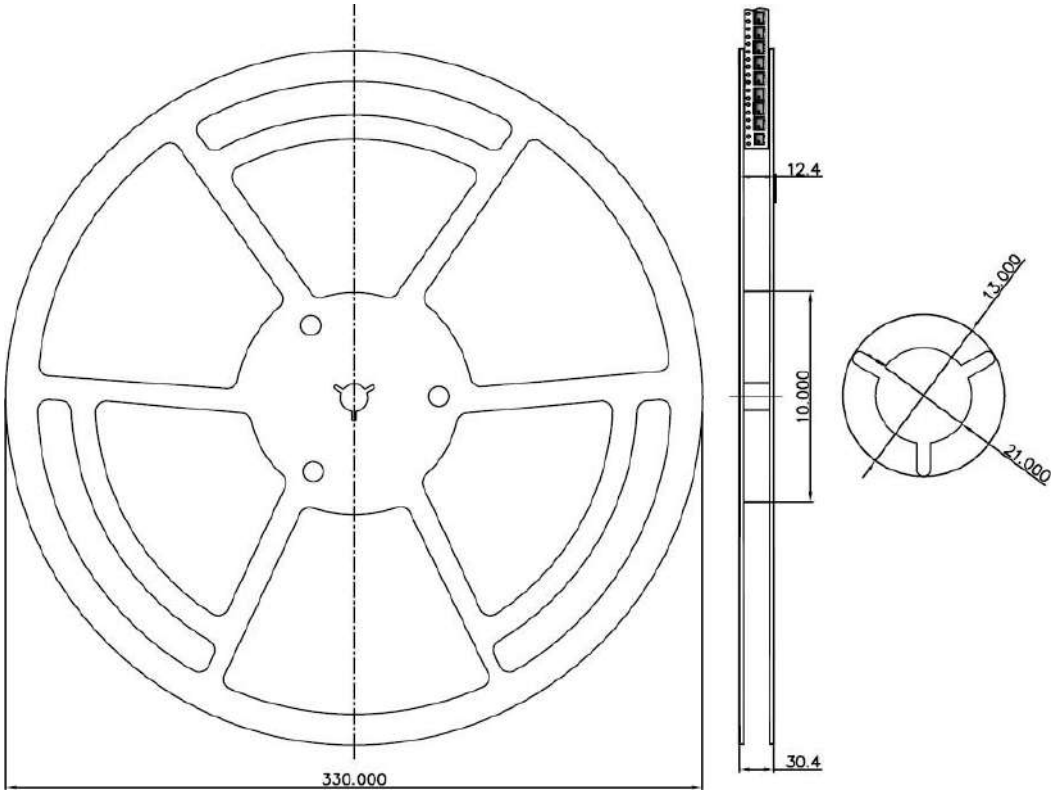
8-Lead DFN5×6 Plastic Package



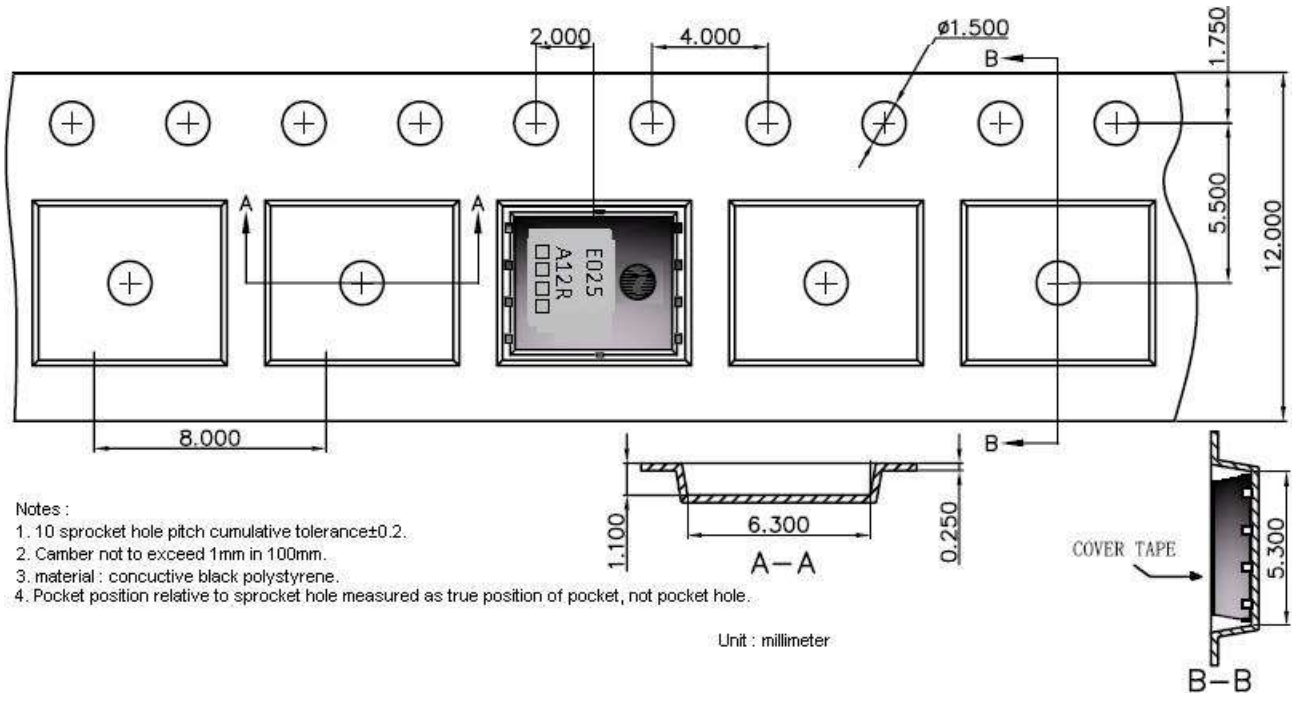
Recommended Soldering Footprint

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.035	0.039	0.900	1.000	k	0.047	0.055	1.190	1.390
A3	0.010	REF.	0.254	REF.	b	0.014	0.018	0.350	0.450
D	0.195	0.201	4.944	5.096	e	0.050	TYP.	1.270	TYP.
E	0.235	0.241	5.974	6.126	L	0.020	0.028	0.559	0.711
D1	0.154	0.162	3.910	4.110	L1	0.017	0.023	0.424	0.576
E1	0.133	0.141	3.375	3.575	H	0.023	0.029	0.574	0.726
D2	0.190	0.196	4.824	4.976	θ	8°	12°	8°	12°
E2	0.223	0.229	5.674	5.826					

Reel Dimension



Carrier Tape Dimension



Notes :
1. 10 sprocket hole pitch cumulative tolerance±0.2.
2. Camber not to exceed 1mm in 100mm.
3. material : concuctive black polystyrene.
4. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

Unit : millimeter